SN74ALVCHG162282 **18-BIT TO 36-BIT REGISTERED BUS EXCHANGER** WITH 3-STATE OUTPUTS

SCES094C – FEBRUARY 1997 – REVISED JUNE 199

 Member of the Texas Instruments Widebus™ Family 		BB PAC (TOP VI		E
 EPIC[™] (Enhanced-Performance Implanted CMOS) Sub-Micron Process 	V _{CC} [GND [] v _{cc}] gnd
 A-Port Outputs Have Equivalent 50-Ω 	2B9		- F] 1B10
Series Resistors and B-Port Outputs Have	1B9 🛛	4	77] 2B10
Equivalent 20-Ω Series Resistors, So No	2B8 🛛		L] 1B11
External Resistors Are Required	GND		L	GND
ESD Protection Exceeds 2000 V Per	1B8			2B11
MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)	2B7 L			1B12
		9		2B12
 Latch-Up Performance Exceeds 250 mA Per JESD 17 		10 11] V _{CC}] 1B13
	286 U 186 U			2B13
 Bus-Hold On Data Inputs Eliminates the Need for External Pullup/Pulldown] 1B14
Resistors	Н] 2B14
	н] GND
 Packaged in Thin Very Small-Outline Package 	н] 1B15
	1B4 🛛	17	64] 2B15
NOTE: For order entry:	2B3 [18	63] 1B16
The DBB package is abbreviated to G.	1B3 🛛	19		2B16
For tape and reel:		20		V _{CC}
The DBBR package is abbreviated to GR.	GND L			GND
description	1	22] 1B17
description	· 7	23		2B17
The SN74ALVCHG162282 is an 18-bit to 36-bit				1B18
registered bus exchanger. This device is intended		25 26] 2B18
for use in applications where data must be] V _{CC}] A18
transferred from a narrow high-speed bus to a			- P	A10 A17
wide lower-frequency bus. It is designed	A2 [A16
specifically for low-voltage (3.3-V) V_{CC} operation.				GND
The device provides synchronous data exchange				A15
between the two ports. Data is stored in the	4	32		A14
internal registers on the low-to-high transition of	3	33] A13

the clock (CLK) input. For data transfer in the B-to-A direction, the select (SEL) input selects 1B or 2B data for the A outputs.

For data transfer in the A-to-B direction, a two-stage pipeline is provided in the 1B path, with a single storage register in the 2B path. Data flow is controlled by the active-low output-enable (\overline{OE}) and direction-control (DIR) input. DIR is registered to synchronize the bus direction changes with the clock.

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47] V_{CC}

46 🛛 A12

45 🛛 A11

44 🛛 A10

43 GND

42 0E

41] DIR

34

35

36 A8 🛛

38

39

40

Vcc

Α7

A9 🛛 37

GND

CLK

SEL Ш

description (continued)

The A-port N-channel output transistors are sized at 450 μ m and the P-channel output transistors are sized at 700 μ m. All A-port outputs have equivalent 50- Ω series resistors. The B-port N-channel output transistors are sized at 225 μ m, and the P-channel output transistors are sized at 560 μ m. All B-port outputs have equivalent 20- Ω series resistors.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The switching characteristics are based on 25-pF (A port) and 80-pF (B port) loads, but are tested with the standard 50-pF load.

The SN74ALVCHG162282 is characterized for operation from 0°C to 70°C.

Function Tables

A-TO-B STORAGE $(\overline{OE} = L, DIR = H)$

(OL = L, DIX = II)							
I	NPUTS	OUTI	PUTS				
SEL	CLK	Α	1B	2B			
н	Х	Х	1B0†	2B0†			
L	\uparrow	L	L‡	L			
L	\uparrow	Н	H‡	Н			
+0.00	L	1.0		. P 1			

[†]Output level before indicated steady-state input conditions were established

[‡] Two CLK edges are needed to propagate the data.

B-TO-A STORAGE($\overline{OE} = L, DIR = L$)

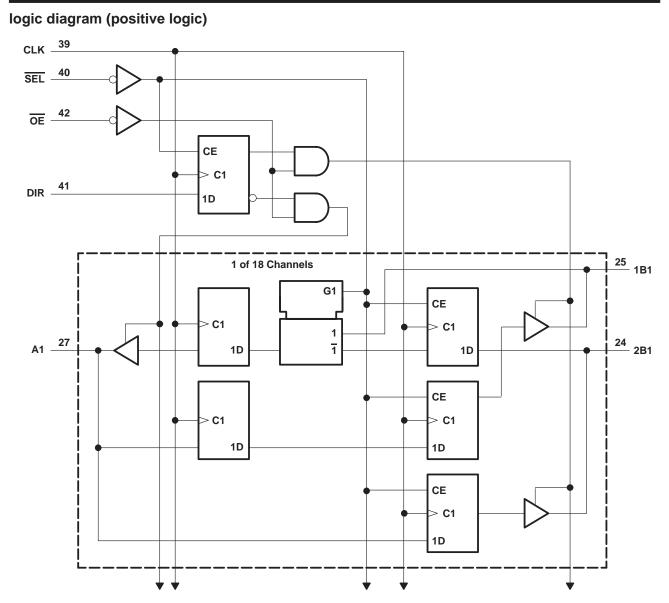
	INPUTS				
CLK	SEL	1B	2B	Α	
↑	Н	Х	L	L§	
↑	Н	Х	н	Н§	
↑	L	L	Х	L	
↑	L	Н	Х	н	

§ Two CLK edges are needed to propagate the data. The data is loaded in the first register when SEL is low and propagates to the second register when SEL is high.

OUTPUT ENABLE

INPUTS			OUT	PUTS
CLK	OE	DIR	Α	1B, 2B
↑	Н	Х	Z	Z
\uparrow	L	Н	z	Active
\uparrow	L	L	Active	Z







absolute maximum ratings over operating free-air temperature (unless otherwise noted)[†]

Supply voltage range, V _{CC}	
Input voltage range, V _I : Except I/O ports (see Note 1) I/O ports (see Notes 1 and 2)	$-0.5 \vee \text{to } \vee_{\text{CC}} + 0.5 \vee \text{to } \vee_{$
Output voltage range, V _O (see Notes 1 and 2)	–0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I_{OK} (V _O < 0)	
Continuous output current, I _O	±50 mA
Package thermal impedance, θ _{JA} (see Note 3)	106°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. The input and output positive voltage ratings may be exceeded up to 4.6 V if the input and output clamp-current ratings are observed.

3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
Vcc	Supply voltage		3	3.6	V
VIH	High-level input voltage V _{CC} = 3 V	2		V	
VIL	Low-level input voltage V _{CC} = 3 V	to 3.6 V		0.8	V
VI	VI Input voltage				
Vo	Output voltage				V
	High-level output current A to B V _{CC} = 3 V			8	mA
ЮН	B to A $V_{CC} = 3 V$			6	ША
	Low-level output current A to B V _{CC} = 3 V			8	mA
IOL	B to A $V_{CC} = 3 V$		6	ША	
$\Delta t/\Delta v$	Input transition rise or fall rate			10	ns/V
ТА	Operating free-air temperature		0	70	°C

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



	ise noted)	ensites over recommended operating ne			inge (unicoo
PAF	RAMETER	TEST CONDITIONS	Vcc	MIN TYP [†]	MAX	UNIT
		I _{OH} = -100 μA	3 V to 3.6 V	V _{CC} -0.2		
VOH	A to B	$I_{OH} = -8 \text{ mA}$	3 V	2		V
	B to A		3.\/	2		

electrical characteristics over recommended operating free-air temperature range (unless

∨он	A to B	I _{OH} = -8 mA	= -8 mA		2		V
	B to A	I _{OH} = -6 mA		3 V	2		
		I _{OL} = 100 μA		3 V to 3.6 V		0.2	
VOL	A to B	I _{OL} = 8 mA		3 V		0.8	V
	B to A	I _{OL} = 6 mA		3 V		0.8	
Ц		$V_I = V_{CC}$ or GND		3.6 V		±5	μA
		V _I = 0.8 V		3 V	75		
II(hold)		V _I = 2 V		3 V	-75		μA
		$V_{I} = 0$ to 3.6 V [‡]		3.6 V		±500	
Ioz§		$V_{O} = V_{CC}$ or GND		3.6 V		±10	μΑ
ICC		$V_{I} = V_{CC} \text{ or GND},$	IO = 0	3.6 V		40	μA
∆ICC	_	One input at V _{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V		750	μA
Ci	Control inputs	$V_{I} = V_{CC} \text{ or } GND$		3.3 V		4	pF
C _{io}	A or B ports	$V_{O} = V_{CC} \text{ or } GND$		3.3 V	8.	5	pF

⁺ All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

[‡] This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another. § For I/O ports, the parameter IOZ includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

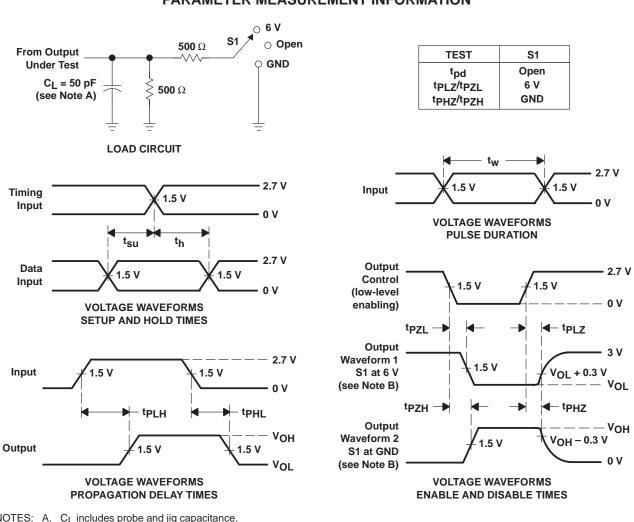
			V _{CC} = ± 0.		UNIT	
			MIN	MAX		
fclock	Clock frequency			160	MHz	
tw	Pulse duration, CLK high or low		2.3		ns	
		A data before CLK↑	1.5			
	Setup time, high or low	B data before CLK↑	2		ns	
t _{su}		DIR before CLK↑	2			
		SEL before CLK↑	2			
		A data after CLK↑	0.3			
		B data after CLK↑	0.3			
th	Hold time, high or low	DIR after CLK↑	0.3		ns	
		SEL after CLK↑	0.3			



switching characteristics over recommended operating free-air temperature range, $C_L = 25 \text{ pF}$ (A port), 80 pF (B port) (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)			V _{CC} = ± 0.3	UNIT
		(001-01)	MIN	MAX	
fmax			160		MHz
+ .	CLK	A	1.5	5	200
^t pd	CER	В	1.5	7.4	ns
	CLK OE	A	1.5	6.3	ns
		В	1.5	9.4	
^t en		A	1.5	6	
		В	1.5	9.5	
	01.1%	A	1.5	6.4	
A	CLK	В	1.5	7.8	
^t dis		A	1.5	5	ns
	ŌE	В	1.5	7.6	





PARAMETER MEASUREMENT INFORMATION

- NOTES: A. CL includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r \leq 2.5 ns, t_f \leq 2.5 ns.
 - D. The output is measured with one input transition per measurement.
 - E. tpLZ and tpHZ are the same as tdis.
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. tPLH and tPHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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